

Chee Wee Liu

List of Publications by Year in descending order

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328
docs citations

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times ranked

4066
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical Measurements to Detect Liquid Concentration. IEEE Transactions on Semiconductor Manufacturing, 2022, 35, 11-15.	1.7	0
2	Performance Improvement by Double-Layer a-IGZO TFTs With a Top Barrier. IEEE Journal of the Electron Devices Society, 2022, 10, 45-50.	2.1	2
3	Highly Stacked GeSn Nanosheets by CVD Epitaxy and Highly Selective Isotropic Dry Etching. IEEE Transactions on Electron Devices, 2022, 69, 2130-2136.	3.0	5
4	Engineering Hf _{0.5} Zr _{0.5} O ₂ Ferroelectric/Anti-Ferroelectric Phases With Oxygen Vacancy and Interface Energy Achieving High Remanent Polarization and Dielectric Constants. IEEE Electron Device Letters, 2022, 43, 553-556.	3.9	19
5	Experimental Demonstration of TreeFETs Combining Stacked Nanosheets and Low Doping Interbridges by Epitaxy and Wet Etching. IEEE Electron Device Letters, 2022, 43, 682-685.	3.9	13
6	Boost of orthorhombic population with amorphous SiO ₂ interfacial layer—a DFT study. Semiconductor Science and Technology, 2022, 37, 05LT01.	2.0	4
7	Spin effect on the low-temperature resistivity maximum in a strongly interacting 2D electron system. Scientific Reports, 2022, 12, 5080.	3.3	2
8	Cell Stability and Write Improvement of 2T (Footprint) Stacked SRAM. , 2022, , .		0
9	RF Performance Optimization of Stacked Si Nanosheet nFETs. , 2022, , .		3
10	RF Performance of Stacked Si Nanosheets/Nanowires. IEEE Electron Device Letters, 2022, 43, 1017-1020.	3.9	9
11	Self-Heating of FinFET Circuitry Simulated by Multi-Correlated Recurrent Neural Networks. IEEE Electron Device Letters, 2022, 43, 1179-1182.	3.9	0
12	Self-Heating Mitigation of TreeFETs by Interbridges. IEEE Transactions on Electron Devices, 2022, 69, 4123-4128.	3.0	8
13	Multi- <i>V_T</i> of Stacked GeSn Nanosheets by ALD WN _x C _y Work Function Metal. IEEE Transactions on Electron Devices, 2022, 69, 3611-3616.	3.0	0
14	Thermally Robust Perpendicular SOT-MTJ Memory Cells With STT-Assisted Field-Free Switching. IEEE Transactions on Electron Devices, 2021, 68, 6623-6628.	3.0	5
15	Highly Stacked GeSi Nanosheets and Nanowires by Low-Temperature Epitaxy and Wet Etching. IEEE Transactions on Electron Devices, 2021, 68, 6599-6604.	3.0	9
16	Valley effects on the fractions in an ultrahigh mobility SiGe/Si/SiGe two-dimensional electron system. Physical Review B, 2021, 103, .	3.2	3
17	Uniform 4-Stacked Ge _{0.9} Sn _{0.1} Nanosheets Using Double Ge _{0.95} Sn _{0.05} Caps by Highly Selective Isotropic Dry Etch. IEEE Transactions on Electron Devices, 2021, 68, 2071-2076.	3.0	9
18	Double-Layer Amorphous InGaZnO Thin Film Transistors with High Mobility and High Reliability. , 2021, , .		1

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19	Architecture and Optimization of 2T (Footprint) SRAM. IEEE Transactions on Electron Devices, 2021, 68, 4918-4924.	3.0	4
20	RF Performance of Stacked Si Nanosheet nFETs. IEEE Transactions on Electron Devices, 2021, 68, 5277-5283.	3.0	14
21	Bilayer-Based Antiferroelectric HfZrO ₂ Tunneling Junction With High Tunneling Electroresistance and Multilevel Nonvolatile Memory. IEEE Electron Device Letters, 2021, 42, 1464-1467.	3.9	19
22	Energy preference of uniform polarization switching for HfO ₂ by first-principle study. Journal Physics D: Applied Physics, 2021, 54, 085304.	2.8	15
23	Critical Current Reduction of Field-Free Perpendicular SOT-MTJ by STT Assist Using Micromagnetic Simulation. , 2021, , .		1
24	Density dependence of the excitation gaps in an undoped Si/SiGe double-quantum-well heterostructure. Applied Physics Letters, 2021, 119, 223103.	3.3	0
25	Highly Stacked 8 Ge _{0.9} Sn _{0.1} Nanosheet pFETs with Ultrathin Bodies (~3nm) and Thick Bodies (~30nm) Featuring the Respective Record I_{ON}/I_{OFF} of 1.4×10^7 and Record I_{ON} of $92 \mu A$ at $I_{OFF} = 0.5 \mu A$ by CVD Epitaxy and Dry Etching. , 2021, , .		1
26	On-Current Enhancement in TreeFET by Combining Vertically Stacked Nanosheets and Interbridges. IEEE Electron Device Letters, 2020, 41, 1292-1295.	3.9	18
27	Infrared Response of Stacked GeSn Transistors. , 2020, , .		0
28	Optical Detection of Parasitic Channels of Vertically Stacked Ge _{0.98} Si _{0.02} nGAAFETs. IEEE Transactions on Electron Devices, 2020, 67, 4073-4078.	3.0	2
29	Low Contact Resistivity to Ge Using <i>In-Situ</i> B and Sn Incorporation by Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2020, 67, 5053-5058.	3.0	4
30	Ab Initio Study on Tuning the Ferroelectricity of Orthorhombic HfO ₂ . , 2020, , .		0
31	Oxygen-related Reliability of Amorphous InGaZnO Thin Film Transistors. IEEE Journal of the Electron Devices Society, 2020, , 1-1.	2.1	11
32	Different Infrared Responses From the Stacked Channels and Parasitic Channel of Stacked GeSn Channel Transistors. IEEE Electron Device Letters, 2020, 41, 147-150.	3.9	3
33	Strain effect on the stability in ferroelectric HfO ₂ simulated by first-principles calculations. Journal Physics D: Applied Physics, 2020, 53, 23LT01.	2.8	28
34	Thermoelectric transport of the half-filled lowest Landau level in a p-type Ge/SiGe heterostructure. Physical Review B, 2020, 101, .	3.2	1
35	Novel vertically stacked Ge _{0.85} Si _{0.15} nGAAFETs above a Si channel with low SS of 76 mV/dec by underneath Si channel and enhanced I_{ON} (1.7X at $V_{OV} = V_{DS} = 0.5$ V) by Ge _{0.85} Si _{0.15} channels. Semiconductor Science and Technology, 2020, 35, 055010.	2.0	1
36	First Demonstration of 4-Stacked Ge _{0.915} Sn _{0.085} Wide Nanosheets by Highly Selective Isotropic Dry Etching with High S/D Doping and Undoped Channels. , 2020, , .		3

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37	Thermal SPICE Modeling of FinFET and BEOL Considering Frequency-Dependent Transient Response, 3-D Heat Flow, Boundary/Alloy Scattering, and Interfacial Thermal Resistance. IEEE Transactions on Electron Devices, 2019, 66, 2710-2714.	3.0	18
38	Effects of Annealing Temperature and Nitrogen Content on Effective Work Function of Tungsten Nitride. IEEE Electron Device Letters, 2019, 40, 1237-1240.	3.9	4
39	Theoretical calculation of ferroelectric $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ by first-principle molecular dynamic simulation. Materials Research Express, 2019, 6, 095045.	1.6	6
40	Record Low Contact Resistivity ($4.4\text{Å} - 10^{10}\text{Ω}\cdot\text{cm}^2$) to Ge Using In-situ B and Sn Incorporation by CVD With Low Thermal Budget ($\sim 400\text{Å}^\circ\text{C}$) and Without Ga. , 2019, , .		0
41	Mobility Enhancement of Back-Channel-Etch Amorphous InGaZnO TFT by Double Layers With Quantum Well Structures. IEEE Transactions on Electron Devices, 2019, 66, 4188-4192.	3.0	24
42	First Stacked $\text{Ge}_{0.88}\text{Sn}_{0.12}$ pGAAFETs with Cap, LG=40nm, Compressive Strain of 3.3%, and High S/D Doping by CVD Epitaxy Featuring Record ION of $58\text{Å}\mu\text{A}$ at $V_{\text{OV}}=V_{\text{DS}}=-0.5\text{V}$, Record $G_{\text{m,max}}$ of $172\text{Å}\mu\text{S}$ at $V_{\text{DS}}=-0.5\text{V}$, and Low Noise. , 2019, , .		4
43	First Vertically Stacked Tensily Strained $\text{Ge}_{0.98}\text{Si}_{0.02}$ nGAAFETs with No Parasitic Channel and $L_{\text{G}}=40\text{ nm}$ Featuring Record $I_{\text{ON}}=48\text{ Å}^2$ at $V_{\text{OV}}=V_{\text{DS}}=0.5\text{V}$ and Record $G_{\text{m,max}}(\frac{1}{4}\text{S}/\frac{1}{4}\text{m})/SS_{\text{SAT}}(\text{mV}/\text{dec})=8.3$ at $V_{\text{DS}}=0.5\text{V}$. , 2019, , .		5
44	Self-Heating Induced Interchannel V_{t} Difference of Vertically Stacked Si Nanosheet Gate-All-Around MOSFETs. IEEE Electron Device Letters, 2019, 40, 1913-1916.	3.9	13
45	Write Margin Analysis of Spin-Orbit Torque Switching Using Field-Assisted Method. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2019, 5, 173-181.	1.5	2
46	Extremely Steep Switch of Negative-Capacitance Nanosheet GAA-FETs and FinFETs. , 2018, , .		33
47	Mobility Calculation of Ge Nanowire Junctionless and Inversion-Mode Nanowire NFETs With Size and Shape Dependence. IEEE Transactions on Electron Devices, 2018, 65, 5295-5300.	3.0	6
48	Comprehensive Thermal SPICE Modeling of FinFETs and BEOL with Layout Flexibility Considering Frequency Dependent Thermal Time Constant, 3D Heat Flows, Boundary/Alloy Scattering, and Interfacial Thermal Resistance with Circuit Level Reliability Evaluation. , 2018, , .		5
49	Fractional Quantum Hall Effect in SiGe/Si/SiGe Quantum Wells in Weak Quantizing Magnetic Fields. JETP Letters, 2018, 107, 794-797.	1.4	4
50	Mobility calculation of Ge nanowire junctionless NFETs with size and geometry dependence. , 2018, , .		1
51	Dopant Recovery in Epitaxial Ge on SOI by Laser Annealing With Device Applications. IEEE Transactions on Electron Devices, 2018, 65, 2925-2931.	3.0	3
52	Vertically Stacked Strained 3-GeSn-Nanosheet pGAAFETs on Si Using GeSn/Ge CVD Epitaxial Growth and the Optimum Selective Channel Release Process. IEEE Electron Device Letters, 2018, 39, 1274-1277.	3.9	25
53	Biaxial strain effects on photoluminescence of Ge/strained GeSn/Ge quantum well. Optical Materials Express, 2018, 8, 2795.	3.0	4
54	Atomic-layer doping of SiGe heterostructures for atomic-precision donor devices. Physical Review Materials, 2018, 2, .	2.4	1

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55	Band alignments at strained Ge _{1-x} Sn _x /relaxed Ge _{1-y} Sn _y heterointerfaces. Journal Physics D: Applied Physics, 2017, 50, 13LT02.	2.8	16
56	Interface Trap Density Reduction Due to AlGeO Interfacial Layer Formation by Al Capping on Al ₂ O ₃ /GeO ₂ /Ge Stack. IEEE Transactions on Electron Devices, 2017, 64, 1412-1417.	3.0	4
57	High-Mobility CVD-Grown Ge _{0.9} Sn _{0.1} /Ge Quantum-Well pMOSFETs on Si by Optimizing Ge Cap Thickness. IEEE Transactions on Electron Devices, 2017, 64, 2498-2504.	3.0	25
58	Effective g factor of low-density two-dimensional holes in a Ge quantum well. Applied Physics Letters, 2017, 111, .	3.3	18
59	Density-controlled quantum Hall ferromagnetic transition in a two-dimensional hole system. Scientific Reports, 2017, 7, 2468.	3.3	9
60	Indication of band flattening at the Fermi level in a strongly correlated electron system. Scientific Reports, 2017, 7, 14539.	3.3	25
61	Process Simulation of Pulsed Laser Annealing on Epitaxial Ge on Si. ECS Journal of Solid State Science and Technology, 2017, 6, P495-P498.	1.8	2
62	Semiconductor, topological semimetal, indirect semimetal, and topological Dirac semimetal phases of $\text{Ge}_{1-x}\text{Sn}_x$ alloys. Physical Review B, 2017, 95, .	3.2	25
63	Unusual anisotropy of inplane field magnetoresistance in ultra-high mobility SiGe/Si/SiGe quantum wells. Journal of Applied Physics, 2017, 122, 224301.	2.5	11
64	Abnormal Threshold Voltage Shift of Amorphous InGaZnO Thin-Film Transistors Due to Mobile Sodium. IEEE Journal of the Electron Devices Society, 2016, 4, 353-357.	2.1	8
65	Thermal resistance modeling of back-end interconnect and intrinsic FinFETs, and transient simulation of inverters with capacitive loading effects. , 2016, , .		28
66	Photoluminescence and electroluminescence from Ge/strained GeSn/Ge quantum wells. Applied Physics Letters, 2016, 109, .	3.3	10
67	Magneto-transport analysis of an ultra-low-density two-dimensional hole gas in an undoped strained Ge/SiGe heterostructure. Applied Physics Letters, 2016, 108, .	3.3	21
68	Low contact resistivity ($1.5\text{Å} - 10^8 \text{Î©}\cdot\text{cm}^2$) of phosphorus-doped Ge by in-situ chemical vapor deposition doping and laser annealing. , 2016, , .		1
69	Physical thickness 1.x nm ferroelectric HfZrOx negative capacitance FETs. , 2016, , .		105
70	Record high mobility ($428\text{cm}^2/\text{V}\cdot\text{s}$) of CVD-grown Ge/strained Ge _{0.91} Sn _{0.09} /Ge quantum well p-MOSFETs. , 2016, , .		6
71	Ga content and thickness inhomogeneity effects on Cu(In, Ga)Se ₂ solar modules. Electronic Materials Letters, 2016, 12, 506-511.	2.2	0
72	Electron Mobility in Junctionless Ge Nanowire NFETs. IEEE Transactions on Electron Devices, 2016, 63, 4191-4195.	3.0	8

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73	Strain-enhanced inhomogeneity effects on CIGS solar modules. , 2016, , .		0
74	Modeling and simulation of TSV induced keep-out zone using silicon data. , 2016, , .		0
75	High-mobility capacitively-induced two-dimensional electrons in a lateral superlattice potential. Scientific Reports, 2016, 6, 20967.	3.3	2
76	Compact modeling and simulation of TSV with experimental verification. , 2016, , .		1
77	The hysteresis-free negative capacitance field effect transistors using non-linear poly capacitance. Solid-State Electronics, 2016, 122, 13-17.	1.4	8
78	Passivation of Al ₂ O ₃ on TiO ₂ on monocrystalline Si with relatively low reflectance. Journal Physics D: Applied Physics, 2016, 49, 245105.	2.8	3
79	Suppression of surface recombination in CuInSe ₂ (CIS) thin films via Trioctylphosphine Sulfide (TOP:S) surface passivation. Acta Materialia, 2016, 106, 171-181.	7.9	13
80	Investigation of optical parameters of boron doped aluminium nitride films grown on diamond using spectroscopic ellipsometry. International Journal of Nanotechnology, 2015, 12, 97.	0.2	2
81	Advanced germanium channel transistors (invited). , 2015, , .		0
82	Scattering mechanisms in shallow undoped Si/SiGe quantum wells. AIP Advances, 2015, 5, .	1.3	29
83	Junctionless Gate-all-around pFETs on Si with In-situ doped Ge channel. , 2015, , .		1
84	Antireflection of nano-sized SiO sphere arrays on crystalline silicon solar cells. , 2015, , .		1
85	The $\sim 3 \times 10^{20}$ cm ⁻³ Electron Concentration and Low Specific Contact Resistivity of Phosphorus-Doped Ge on Si by <i>In-Situ Chemical Vapor Deposition Doping and Laser Annealing</i> . IEEE Electron Device Letters, 2015, 36, 1114-1117.	3.9	37
86	Junctionless Gate-All-Around pFETs Using <i>In-situ</i> Boron-Doped Ge Channel on Si. IEEE Nanotechnology Magazine, 2015, 14, 878-882.	2.0	26
87	Ultra-high mobility two-dimensional electron gas in a SiGe/Si/SiGe quantum well. Applied Physics Letters, 2015, 106, .	3.3	30
88	Magneto-transport of an electron bilayer system in an undoped Si/SiGe double-quantum-well heterostructure. Applied Physics Letters, 2015, 106, 143503.	3.3	6
89	Reply to "Comment on "A Compact Analytic Model of the Strain Field Induced by Through Silicon Vias". IEEE Transactions on Electron Devices, 2015, 62, 3106-3106.	3.0	0
90	Asymmetric Keep-Out Zone of Through-Silicon Via Using 28-nm Technology Node. IEEE Electron Device Letters, 2015, 36, 938-940.	3.9	5

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91	(Invited) Gate-All-Around Ge FETs. ECS Transactions, 2014, 64, 317-328.	0.5	1
92	Effective electron mass in high-mobility SiGe/Si/SiGe quantum wells. JETP Letters, 2014, 100, 114-119.	1.4	13
93	Ge gate-all-around FETs on Si. , 2014, , .		0
94	Fabrication and characterization of Cu(In,Ga)Se ₂ p-channel thin film transistors. Applied Physics Letters, 2014, 105, 143502.	3.3	3
95	In-situ doped and tensily strained Ge junctionless gate-all-around nFETs on SOI featuring $\mu_{\text{eff}} = 828 \text{ cm}^2/\text{Vs}$, $\mu_{\text{off}} = 10 \text{ cm}^2/\text{Vs}$, DIBL= 16 mV/V , and 1.4X external strain enhancement. , 2014, , .		5
96	Ballistic electron transport calculation of strained germanium-tin fin field-effect transistors. Applied Physics Letters, 2014, 104, .	3.3	12
97	Hysteresis reduction by fluorine incorporation into high permittivity tetragonal ZrO ₂ on Ge. Applied Physics Letters, 2014, 104, 032902.	3.3	5
98	Electron ballistic current enhancement of Ge _{1-x} Sn _x FinFETs. , 2014, , .		0
99	Fabrication and Low Temperature Characterization of Ge (110) and (100) p-MOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 2215-2219.	3.0	21
100	New materials for post-Si computing. MRS Bulletin, 2014, 39, 658-662.	3.5	15
101	Toward Efficient and Omnidirectional n-Type Si Solar Cells: Concurrent Improvement in Optical and Electrical Characteristics by Employing Microscale Hierarchical Structures. ACS Nano, 2014, 8, 2959-2969.	14.6	52
102	Strain response of monolayer MoS ₂ in the ballistic regime. , 2014, , .		0
103	The pn Junctions of Epitaxial Germanium on Silicon by Solid Phase Doping. IEEE Transactions on Electron Devices, 2014, 61, 2595-2598.	3.0	10
104	Reabsorption effects on direct band gap emission from germanium light emitting diodes. , 2014, , .		0
105	Above-11%-Efficiency Organic-Inorganic Hybrid Solar Cells with Omnidirectional Harvesting Characteristics by Employing Hierarchical Photon-Trapping Structures. Nano Letters, 2013, 13, 3658-3663.	9.1	171
106	Germanium Gate-All-Around pFETs on SOI. ECS Transactions, 2013, 50, 31-37.	0.5	1
107	Realizing High-Efficiency Omnidirectional n-Type Si Solar Cells via the Hierarchical Architecture Concept with Radial Junctions. ACS Nano, 2013, 7, 9325-9335.	14.6	94
108	Enhanced Current Drive of Double-Gate α -IGZO Thin-Film Transistors. IEEE Electron Device Letters, 2013, 34, 417-419.	3.9	33

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109	GeO_2 Passivation for Low Surface Recombination Velocity on Ge Surface. IEEE Electron Device Letters, 2013, 34, 444-446.	3.9	14
110	Mobility strain response and low temperature characterization of Ge p-MOSFETs. , 2013, , .		0
111	Improvement in electrical characteristics of HfO ₂ gate dielectrics treated by remote NH ₃ plasma. Applied Surface Science, 2013, 266, 89-93.	6.1	13
112	Modeling and Optimization of Edge Dislocation Stressors. IEEE Electron Device Letters, 2013, 34, 948-950.	3.9	3
113	Radiation Impact of EUV on High-Performance Ge MOSFETs. IEEE Electron Device Letters, 2013, 34, 1220-1222.	3.9	2
114	Temperature dependence of Raman scattering in bulk 4H-SiC with different carrier concentration. Optics Express, 2013, 21, 26475.	3.4	25
115	Interfacial layer reduction and high permittivity tetragonal ZrO ₂ on germanium reaching ultrathin 0.39 nm equivalent oxide thickness. Applied Physics Letters, 2013, 102, .	3.3	16
116	Manganese <i>K</i> - and <i>L</i> -Edge X-Ray Absorption Fine Structure Study of Zn _{1-x} Mn _x Te. Advanced Materials Research, 2013, 634-638, 2489-2492.	0.3	3
117	Study of Mg _x Zn _{1-x} O Alloys (0<x<0.15) by X-Ray Absorption Spectroscopy. Advanced Materials Research, 2013, 663, 361-365.	0.3	6
118	EUV degradation of high performance Ge MOSFETs. , 2013, , .		1
119	Mobility enhancement of strained Si by optimized SiGe/Si/SiGe structures. Applied Physics Letters, 2012, 101, 042111.	3.3	28
120	Ge out diffusion effect on SiGe nanoring formation. Journal of Applied Physics, 2012, 111, 076103.	2.5	0
121	Surface passivation of Cu(In,Ga)Se ₂ using atomic layer deposited Al ₂ O ₃ . Applied Physics Letters, 2012, 100, .	3.3	85
122	Enhanced recovery of light-induced degradation on the micromorph solar cells by electric field. Journal of Applied Physics, 2012, 112, 056104.	2.5	4
123	Influence of surface roughness and interfacial layer on the infrared spectra of V-CVD grown 3C-SiC/Si (100) epilayers. Semiconductor Science and Technology, 2012, 27, 115019.	2.0	8
124	Planar and 3D Ge FETs. , 2012, , .		0
125	A transition of three to two dimensional Si growth on Ge (100) substrate. Journal of Applied Physics, 2012, 112, 126101.	2.5	4
126	SiGe Nanoring Formation. , 2012, , .		0

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127	Interfacial layer-free ZrO ₂ on Ge with 0.39-nm EOT, κ∼43, ∼2×10³/cm²; gate leakage, SS =85 mV/dec, I_{on}/I_{off}, and high strain response., 2012, .		4
128	Reabsorption Effects of Direct Band Emission of Ge., 2012, .		0
129	Triangular-channel Ge NFETs on Si with (111) sidewall-enhanced I_{on} and nearly defect-free channels., 2012, .		9
130	First-principles study of Ge dangling bonds with different oxygen backbonds at Ge/GeO ₂ interface. Journal of Applied Physics, 2012, 111, .	2.5	13
131	Fractional quantum Hall effect of two-dimensional electrons in high-mobility Si/SiGe field-effect transistors. Physical Review B, 2012, 85, .	3.2	21
132	Differential Gene Expression Between the Porcine Morula and Blastocyst. Reproduction in Domestic Animals, 2012, 47, 69-81.	1.4	7
133	Direct and indirect radiative recombination from Ge. Thin Solid Films, 2012, 520, 3249-3254.	1.8	4
134	LDMOS Transistor High-Frequency Performance Enhancements by Strain. IEEE Electron Device Letters, 2012, 33, 471-473.	3.9	15
135	A Compact Analytic Model of the Strain Field Induced by Through Silicon Vias. IEEE Transactions on Electron Devices, 2012, 59, 777-782.	3.0	19
136	Germanium oxide passivation for Ge absorber., 2011, .		1
137	Physical mechanism of HfO ₂ -based bipolar resistive random access memory., 2011, .		11
138	Defect related negative temperature coefficient of short circuit current of Cu(In, Tj)ETQqO O rgBT /Overlock 10 Tf 50 302 Jd (Ga)Se&		
139	Electron scattering in Ge metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 99, .	3.3	13
140	A parameterized SPICE macromodel of resistive random access memory and circuit demonstration., 2011, .		3
141	High quality Ge thin film grown by ultrahigh vacuum chemical vapor deposition on GaAs substrate. Applied Physics Letters, 2011, 98, .	3.3	32
142	Edge Passivation of Si Solar Cells by Omnidirectional Hydrogen Plasma Implantation. Journal of the Electrochemical Society, 2011, 158, H912.	2.9	2
143	Nearly defect-free Ge gate-all-around FETs on Si substrates., 2011, .		11
144	Enhanced optical performance by energetic hydrogen passivation at Si/oxide interface. Thin Solid Films, 2011, 520, 448-451.	1.8	0

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145	Ion implanted boron emitter N-silicon solar cells with wet oxide passivation. , 2011, , .		4
146	Biaxial tensile strain effects on photoluminescence of different orientated Ge wafers. Applied Physics Letters, 2011, 98, .	3.3	21
147	Bifacial CIGS (11% efficiency)/Si solar cells by Cd-free and sodium-free green process integrated with CIGS TFTs. , 2011, , .		5
148	Upper limit of two-dimensional electron density in enhancement-mode Si/SiGe heterostructure field-effect transistors. Applied Physics Letters, 2011, 99, .	3.3	24
149	Influence of defects and interface on radiative transition of Ge. Applied Physics Letters, 2011, 98, 141105.	3.3	17
150	Strain response of high mobility germanium n-channel metal-oxide-semiconductor field-effect transistors on (001) substrates. Applied Physics Letters, 2011, 99, 022106.	3.3	9
151	Voltage Linearity Improvement of HfO ₂ -Based Metal-Insulator-Metal Capacitors with H ₂ O Prepulse Treatment. Journal of the Electrochemical Society, 2011, 158, H128.	2.9	3
152	Toward an ideal animal model to trace donor cell fates after stem cell therapy: Production of stably labeled multipotent mesenchymal stem cells from bone marrow of transgenic pigs harboring enhanced green fluorescence protein1. Journal of Animal Science, 2011, 89, 3460-3472.	0.5	98
153	Insulating Halos to Boost Planar NMOSFET Performance. IEEE Transactions on Electron Devices, 2010, 57, 2526-2530.	3.0	0
154	Threshold Voltage and Mobility Extraction of NBTI Degradation of Poly-Si Thin-Film Transistors. IEEE Transactions on Electron Devices, 2010, 57, 3186-3189.	3.0	2
155	Composition redistribution of self-assembled Ge islands on Si (001) during annealing. Thin Solid Films, 2010, 518, S196-S199.	1.8	8
156	Metal-oxide-semiconductor SiGe/Si quantum dot infrared photodetectors with delta doping in different positions. Thin Solid Films, 2010, 518, S237-S240.	1.8	2
157	Enhanced Voltage Linearity of HfO ₂ Metal-Insulator-Metal Capacitors by H ₂ O Prepulsing Treatment on Bottom Electrode. ECS Transactions, 2010, 33, 83-90.	0.5	1
158	Extrinsic Effects of Indirect Radiative Transition of Ge. ECS Transactions, 2010, 33, 555-562.	0.5	1
159	Enhancements of Direct Band Radiative Recombination from Ge. ECS Transactions, 2010, 33, 563-571.	0.5	0
160	Surface Orientation Effects on SiGe Quantum Dots and Nanorings Formation. ECS Transactions, 2010, 33, 649-659.	0.5	0
161	Integration of complementary circuits and two-dimensional electron gas in a Si/SiGe heterostructure. Applied Physics Letters, 2010, 96, 253103.	3.3	4
162	Capacitorless 1T Memory Cells Using Channel Traps at Grain Boundaries. IEEE Electron Device Letters, 2010, 31, 1125-1127.	3.9	7

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163	Strain-enhanced photoluminescence from Ge direct transition. Applied Physics Letters, 2010, 96, .	3.3	78
164	Thermal oxide, Al ₂ O ₃ and amorphous-Si passivation layers on silicon. , 2010, , .		0
165	Competitiveness between direct and indirect radiative transitions of Ge. Applied Physics Letters, 2010, 96, .	3.3	52
166	Recovery of Light Induced Degradation of Micromorph Solar Cells by Reverse Bias. ECS Transactions, 2010, 33, 57-63.	0.5	0
167	Hexagonal SiGe quantum dots and nanorings on Si(110). Journal of Applied Physics, 2010, 107, 056103.	2.5	9
168	Metal-Insulator-Semiconductor Photodetectors. Sensors, 2010, 10, 8797-8826.	3.8	154
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